

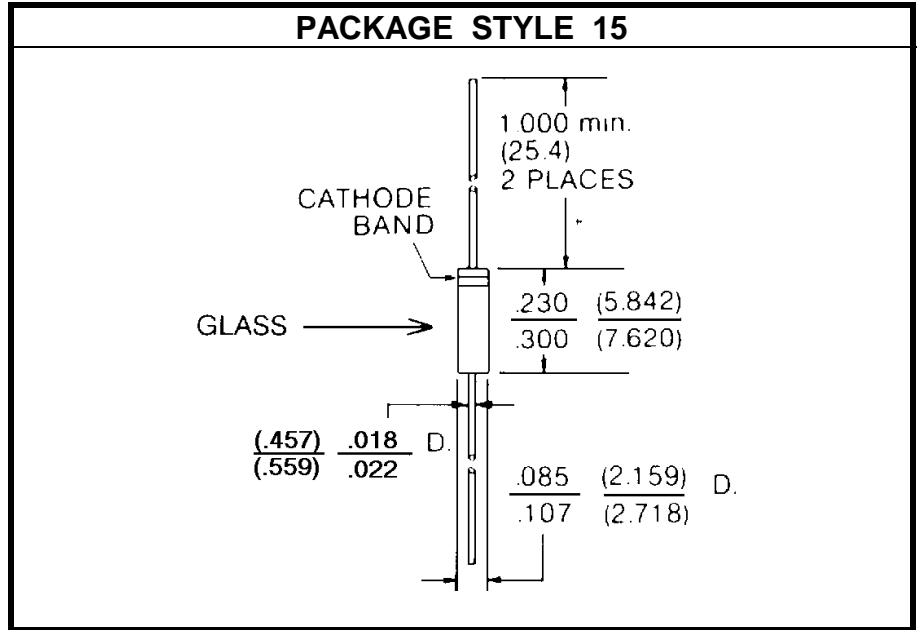
SILICON PIN DIODE

DESCRIPTION:

The **AP1000A** is a Diffused Epitaxial Silicon PIN Diode.

MAXIMUM RATINGS

I_C	100mA
V_{CE}	100 V
P_{DISS}	500 mW @ T _C = 25 °C
T_J	-65 °C to +150 °C
T_{STG}	-65 °C to +175 °C
θ_{JC}	50 °C/W
T_{SOLD}	5.0 Sec./200 °C


CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
V _B	I _R = 10 μA	100			V
C _J	V _R = 6.0 V f = 1.0 MHz			0.05	pF
R _S	I _F = 20 mA I _F = 100 mA f = 1.0 GHz			2.6 2.0	Ohms
T _L	I _F = 10 mA I _R = 6.0 mA		100		nS
T _S	10%-90% / 90%-10%			10	nS
C _P	f = 1.0 MHz		0.15		pF
L _S			2.5		nH